

MKEV008GIB-NY500

eMMC 8GB Specification

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Revision History

Date	Rev	Description
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1. Product List

Capacity	eMMC P/N	NAND Type	User Density	Package Size	Pin
8GB	MKEV008GIB-NY500	64Gb x 1	91.46%	11.5mmx13mmx1.0mm	153 FBGA

2. Key Features

- Compatible to JEDEC Embedded Multi-Media Card (e•MMC) Electrical Standard (5.0)
- Data bus width: 1bit(Default), 4bit and 8bit
- Not support large sector size (4KB)
- Interface power: V_{CCQ} (1.70V~1.95V or 2.7V~3.6V), Memory power: V_{CC} (2.7V~3.6V)
- Temperature: Operation (-40°C~85°C), storage (-40°C~85°C)
- User Density:

eMMC P/N	Density	LBA(Hex)	LBA(Dec)	Capacity(Bytes)
MKEV008GIB-NY500	8GB	EA1FFF	15343615	7855931392

3. Pin Configuration

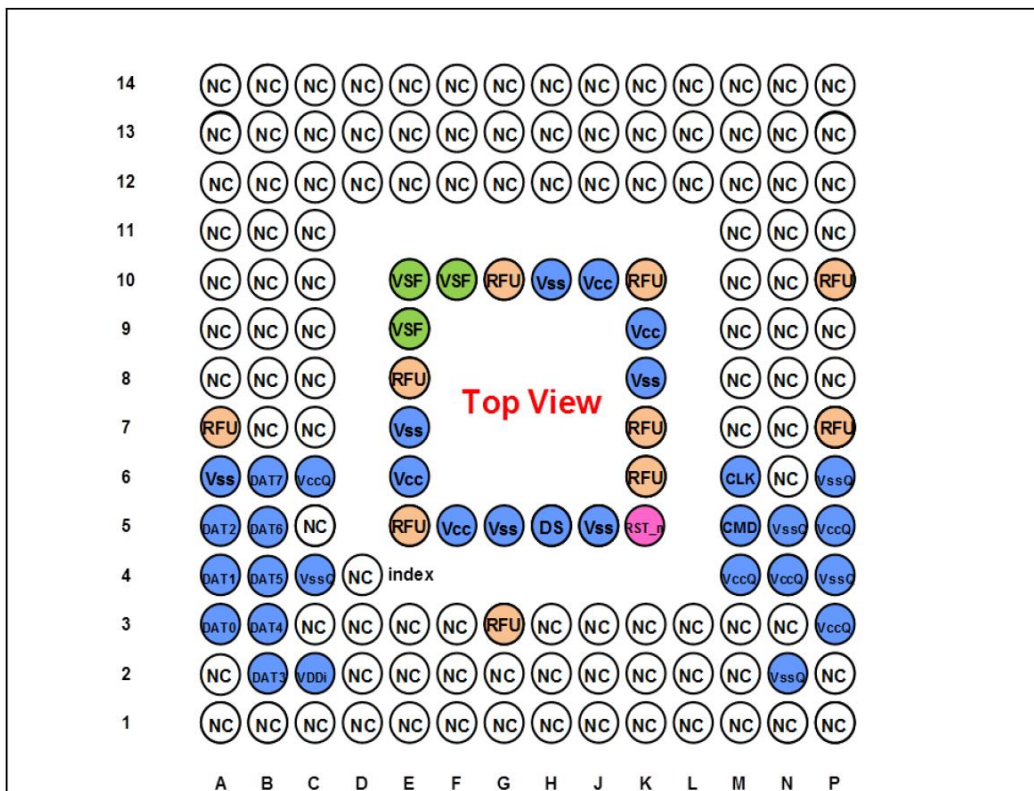


Figure 1 153 FBGA

[Table 1] 153 Ball Information

Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A3	DAT0	C2	VDDi	J5	Vss	N4	VccQ
A4	DAT1	C4	VssQ	J10	Vcc	N5	VssQ
A5	DAT2	C6	VccQ	K5	RST_n	P3	VccQ
A6	Vss	E6	Vcc	K8	Vss	P4	VssQ
B2	DAT3	E7	Vss	K9	Vcc	P5	VccQ
B3	DAT4	F5	Vcc	M4	VccQ	P6	VssQ
B4	DAT5	G5	Vss	M5	CMD		
B5	DAT6	H5	DS	M6	CLK		
B6	DAT7	H10	Vss	N2	VssQ		

4. Package Information

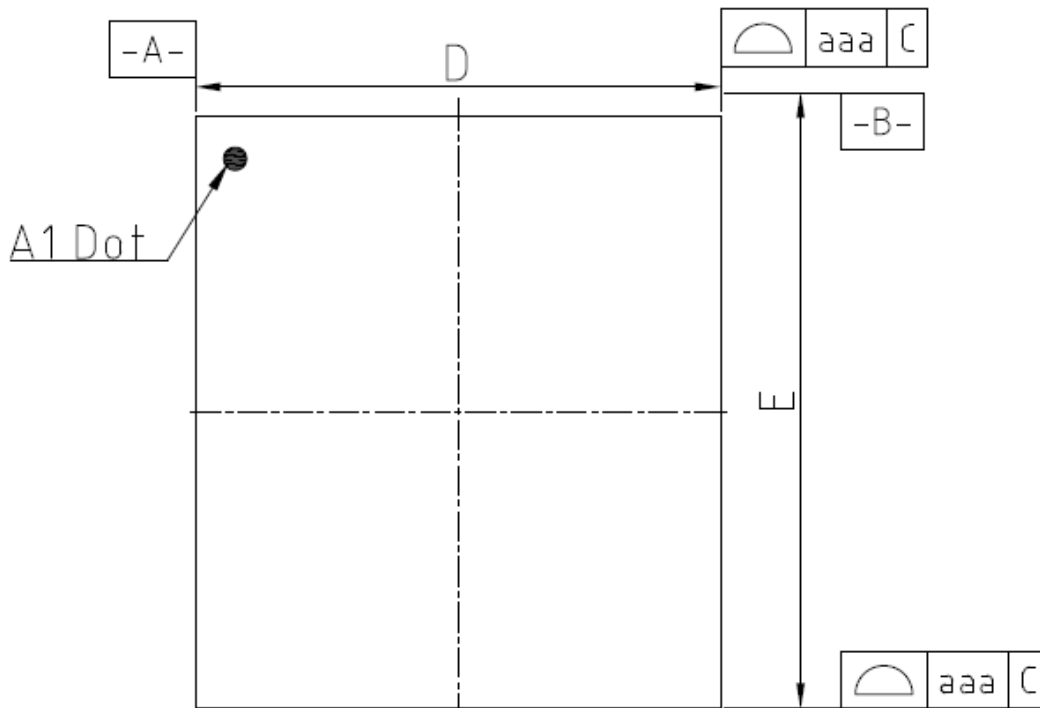


Figure 2 TOP View of Package

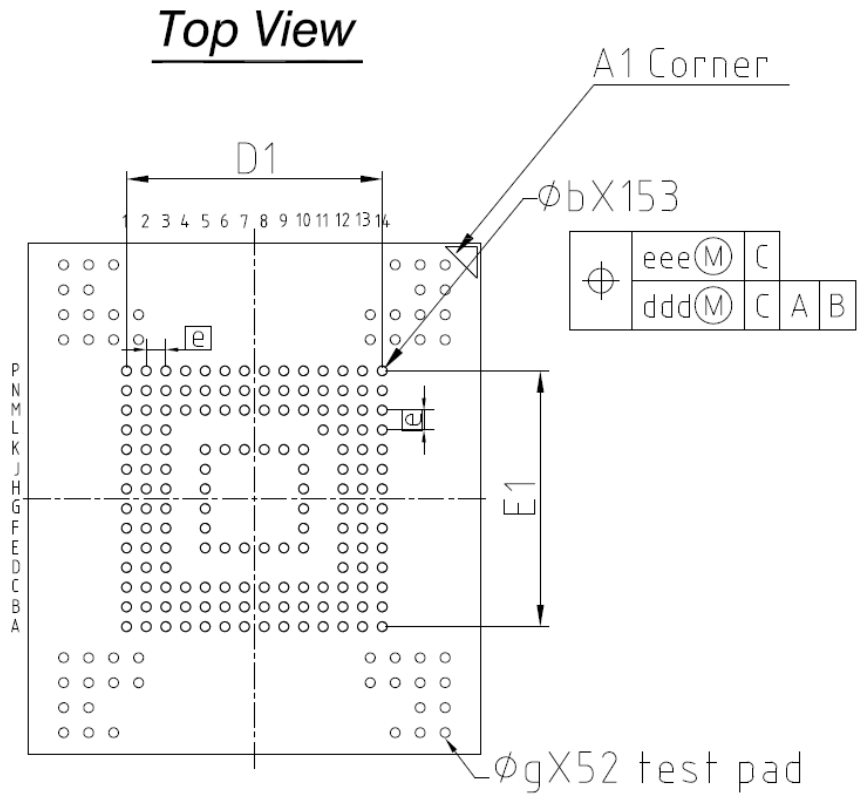


Figure 3 Bottom View of Package

Symbol	Dimension in mm		
	Min	Nom	Max
A	---	---	1.00
A1	0.16	0.21	0.26
A2	0.40	0.42	0.43
c	0.22	0.26	0.30
ϕg	0.25	0.30	0.35
ϕb	0.25	0.30	0.35
D	11.40	11.50	11.60
D1	---	6.50	---
E	12.90	13.00	13.10
E1	---	6.50	---
$\square e$	0.50 BSC		
aaa	0.15		
bbb	0.20		
ccc	0.20		
ddd	0.15		
eee	0.10		



Figure 4 Side View of Package

5. eMMC Register Value

5.1 OCR Register

[Table 2] OCR Register

OCR bit	VDD voltage window	Register Value
[6:0]	Reserved	00 00000b
[7]	1.70 – 1.95	1b
[14:8]	2.0-2.6	000 0000b
[23:15]	2.7-3.6	1 1111 1111b
[28:24]	Reserved	0 0000b
[30:29]	Access Mode	00b (byte mode) 10b (sector mode)
[31]	e.MMC power up status bit	

5.2 CID Register

[Table 3] CID Register

Name	Field	Width	CID-slice	CID Value
Manufacture ID	MID	8	[127:120]	0xEA
Reserved		6	[119:114]	---
Card/BGA	CBX	2	[113:112]	0x01
OEM/Application ID	OID	8	[111:104]	0x0E
Product name	PNM	48	[103:56]	8GB: 901000(0x393031303030)
Product revision	PRV	8	[55:48]	0x10
Product serial number	PSN	32	[47:16]	0x1
Manufacture date	MDT	8	[15:8]	0x13
CRC7 checksum	CRC	7	[7:1]	---
not used, always '1'	-	1	[0:0]	0x1

5.3 CSD Register

[Table 4]CSD Register

Name	Field	Width	Cell Type	CSD-slice	CID Value
CSD Structure	CSD-STRUCTURE	2	R	[127:126]	0x03
System specification version	SPEC_VERS	4	R	[125:122]	0x04
Reserved	-	2	R	[121:120]	-
Data read access-time 1	TAAC	8	R	[119:112]	0x27
Data read access-time 2 in CLK cycles (NSAC*100)	NSAC	8	R	[111:104]	0x00
Max.bus clock frequency	TRAN_SPEED	8	R	[103:96]	0x32
Device command classes	CCC	12	R	[95:84]	0xF5
Max. read data block length	READ_BL_LEN	4	R	[83:80]	0x09
Partial blocks for read allowed	READ_BL_PARTIAL	1	R	[79:79]	0x00
Write block misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]	0x00
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]	0x00
DSR implemented	DSR_IMP	1	R	[76:76]	0x00
Reserved	-	2	R	[75:74]	-
Device size	C_SIZE	12	R	[73:62]	0xFFF
Max. read current@VDD min	VDD_R_CURR_MIN	3	R	[61:59]	0x07
Max. read current@VDD max	VDD_R_CURR_MAX	3	R	[58:56]	0x07
Max. write current@VDD min	VDD_W_CURR_MIN	3	R	[55:53]	0x07
Max. write current@VDD max	VDD_W_CURR_MAX	3	R	[52:50]	0x07
Device size multiplier	C_SIZE_MULT	3	R	[49:47]	0x07
Erase group size	ERASE_GRP_SIZE	5	R	[46:42]	0x1F
Erase group size	ERASE_GRP_MULT	5	R	[41:37]	0x1F

multiplier					
Write Protect group size	WP_GRP_SIZE	5	R	[36:32]	0x07
Write protect group enable	WP_GRP_ENABLE	1	R	[31:31]	0x01
Manufacture default ECC	DEFAULT_ECC	2	R	[30:29]	0x00
Write speed factor	R2W_FACTOR	3	R	[28:26]	0x04
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]	0x09
Partial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]	0x00
Reserved	-	4	R	[20:17]	-
Content protection application	CONTENT_PROT_APP	1	R	[16:16]	0x00
File format group	FILE_FORMAT_GRP	1	R/W	[15:15]	0x00
Copy flag(OTP)	COPY	1	R/W	[14:14]	0x00
Permanent write protection	PERM_WRITE_PROTECT	1	R/W	[13:13]	0x00
Temporary write protection	TMP_WRITE_PROTECT	1	R/W/E	[12:12]	0x00
File Format	FILE_FORMAT	2	R/W	[11:10]	0x00
ECC code	ECC	2	R/W/E	[9:8]	0x00
CRC	CRC	7	R/W/E	[7:1]	0x25
Not used, always '1'	-	1	-	[0:0]	0x1

5.4 Extended CSD Register

[Table 5] Extended CSD Register

Name	Field	Size	Cell Type	CSD-slice	CSD Value
Reserved ¹		6	-	[511:506]	-
Extended Security Commands Error	EXT_SECURITY_ERR	1	R	[505]	0x0
Supported Command Sets	S_CMD_SET	1	R	[504]	0x1
HPI features	HPI_FEATURES	1	R	[503]	0x1
Background operations support	BKOPS_SUPPORT	1	R	[502]	0x0
Max packed read commands	MAX_PACKED_READS	1	R	[501]	0x5
Max packed write commands	MAX_PACKED_WRITES	1	R	[500]	0x5
Data Tag Support	DATA_TAG_SUPPORT	1	R	[499]	0x0
Tag Unit Size	TAG_UNIT_SIZE	1	R	[498]	0x0
Tag Resources Size	TAG_RES_SIZE	1	R	[497]	0x0
Context management capabilities	CONTEXT_CAPABILITIES	1	R	[496]	0x0
Large Unit size	LARGE_UNIT_SIZE_M1	1	R	[495]	0x0
Extended partitions attribute support	EXT_SUPPORT	1	R	[494]	0x0
Supported modes	SUPPORTED_MODES	1	R	[493]	0x1
FFU features	FFU_FEATURES	1	R	[492]	0x1
Operation codes timeout	OPERATION_CODE_TIMEOUT	1	R	[491]	0x10
FFU Argument	FFU_ARG	4	R	[490:487]	0xFE00000
Reserved ¹		181	TBD	[486:306]	0x0
Number of FW sectors correctly programmed	NUMBER_OF_FW_SECTORS_CORRECTLY_PROGRAMMED	4	R	[305:302]	0x0
Vendor proprietary health report	VENDOR_PROPRIETARY_HEALTH_REPORT	32	R	[301:270]	0x0
Device life time estimation type B	DEVICE_LIFE_TIME_EST_TYP_B	1	R	[269]	0x1
Device life time estimation	DEVICE_LIFE_TIME_EST_T	1	R	[268]	0x1

type A	YP_A				
Pre EOL information	PRE_EOL_INFO	1	R	[267]	0x0
Optimal read size	OPTIMAL_READ_SIZE	1	R	[266]	0x4
Optimal write size	OPTIMAL_WRITE_SIZE	1	R	[265]	0x4
Optimal trim unit size	OPTIMAL_TRIM_UNIT_SIZE	1	R	[264]	0x4
Device version	DEVICE_VERSION	2	R	[263:262]	0x1216
Firmware version	FIRMWARE_VERSION	8	R	[261:254]	0x000002021728 1216
Power class for 200MHz, DDR at VCC= 3.6V	PWR_CL_DDR_200_360	1	R	[253]	0x0
Cache size	CACHE_SIZE	4	R	[252:249]	0x0
Generic CMD6 timeout	GENERIC_CMD6_TIME	1	R	[248]	0x5
Power off notification(long) timeout	POWER_OFF_LONG_TIME	1	R	[247]	0x3C
Background operations status	BKOPS_STATUS	1	R	[246]	0x0
Number of correctly programmed sectors	CORRECTLY_PRG_SECTORS_NUM	4	R	[245:242]	0x0
1st initialization time after partitioning	INI_TIMEOUT_AP	1	R	[241]	0xA
Reserved ¹		1	-	[240]	-
Power class for 52MHz, DDR at V _{CC} = 3.6V	PWR_CL_DDR_52_360	1	R	[239]	0x55
Power class for 52MHz, DDR at V _{CC} = 1.95V	PWR_CL_DDR_52_195	1	R	[238]	0x55
Power class for 200MHz at V _{CCQ} =1.95V, V _{CC} = 3.6V	PWR_CL_200_195	1	R	[237]	0x55
Power class for 200MHz at V _{CCQ} =1.3V, V _{CC} = 3.6V	PWR_CL_200_130	1	R	[236]	0x0
Minimum Write Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_W_8_52	1	R	[235]	0x0
Minimum Read Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_R_8_52	1	R	[234]	0x0
Reserved		1	-	[233]	-
TRIM Multiplier	TRIM_MULT	1	R	[232]	0x3

Secure Feature support	SEC_FEATURE_SUPPORT	1	R	[231]	0x55
Secure Erase Multiplier	SEC_ERASE_MULT	1	R	[230]	0x46
Secure TRIM Multiplier	SEC_TRIM_MULT	1	R	[229]	0x3C
Boot information	BOOT_INFO	1	R	[228]	0x7
Reserved		1	-	[227]	_
Boot partition size	BOOT_SIZE_MULT	1	R	[226]	0x20
Access size	ACC_SIZE	1	R	[225]	8GB:0x07
High-capacity erase unit size	HC_ERASE_GRP_SIZE	1	R	[224]	0x1
High-capacity erase timeout	ERASE_TIMEOUT_MULT	1	R	[223]	0x1
Reliable write sector count	REL_WR_SEC_C	1	R	[222]	0x1
High-capacity write protect group size	HC_WP_GRP_SIZE	1	R	[221]	8GB:0x08
Sleep current (VCC)	S_C_VCC	1	R	[220]	0x8
Sleep current (VCCQ)	S_C_VCCQ	1	R	[219]	0x7
Production state awareness timeout	PRODUCTION_STATE_AWARENESS_TIMEOUT	1	R	[218]	0xA
Sleep/awake timeout	S_A_TIMEOUT	1	R	[217]	0x13
Sleep Notification Timeout ¹	SLEEP_NOTIFICATION_TIME	1	R	[216]	0x10
Sector Count	SEC_COUNT	4	R	[215:212]	8GB:0x00EA2000
Reserved	-	1	-	[211]	_
Minimum Write Performance for 8bit at 52MHz	MIN_PERF_W_8_52	1	R	[210]	0x8
Minimum Read Performance for 8bit at 52MHz	MIN_PERF_R_8_52	1	R	[209]	0x8
Minimum Write Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_W_8_26_4_52	1	R	[208]	0x8
Minimum Read Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_R_8_26_4_52	1	R	[207]	0x8
Minimum Write Performance for 4bit at 26MHz	MIN_PERF_W_4_26	1	R	[206]	0x8
Minimum Read Performance for 4bit at 26MHz	MIN_PERF_R_4_26	1	R	[205]	0x8

Reserved		1	-	[204]	_
Power class for 26MHz at 3.6V 1 R	PWR_CL_26_360	1	R	[203]	0x7
Power class for 52MHz at 3.6V 1 R	PWR_CL_52_360	1	R	[202]	0x7
Power class for 26MHz at 1.95V 1 R	PWR_CL_26_195	1	R	[201]	0x7
Power class for 52MHz at 1.95V 1 R	PWR_CL_52_195	1	R	[200]	0x7
Partition switching timing	PARTITION_SWITCH_TIME	1	R	[199]	0x5
Out-of-interrupt busy timing	OUT_OF_INTERRUPT_TIM E	1	R	[198]	0x19
I/O Driver Strength	DRIVER_STRENGTH	1	R	[197]	0x1F
Device type	DEVICE_TYPE		R	[196]	0x57
Reserved1		1	-	[195]	_
CSD STRUCTURE	CSD_STRUCTURE	1	R	[194]	0x2
Reserved ¹		1	TBD	[193]	_
Extended CSD revision	EXT_CSD_REV	1	R	[192]	0x7
Modes Segment					
Command set	CMD_SET	1	R/W/ E_P	[191]	0x0
Reserved ¹		1	TBD	[190]	_
Command set revision	CMD_SET_REV	1	R	[189]	0x0
Reserved ¹		1	TBD	[188]	_
Power class	POWER_CLASS	1	R/W/ E_P	[187]	0x0
Reserved ¹		1	TBD	[186]	_
High-speed interface timing	HS_TIMING	1	R/W/ E_P	[185]	0x0
Reserved ¹		1	TBD	[184]	_
Bus width mode	BUS_WIDTH	1	W/E_ P	[183]	0x0
Reserved ¹		1	TBD	[182]	_
Erased memory content	ERASED_MEM_CONT	1	R	[181]	0x0

Reserved ¹		1	TBD	[180]	–
Partition configuration	PARTITION_CONFIG	1	R/W/ E & R/W/ E_P	[179]	0x0
Boot config protection	BOOT_CONFIG_PROT	1	R/W & R/W/ C_P	[178]	0x0
Boot bus Conditions	BOOT_BUS_CONDITIONS	1	R/W/ E	[177]	0x0
Reserved ¹		1	TBD	[176]	–
High-density erase group definition	ERASE_GROUP_DEF	1	R/W/ E_P	[175]	0x0
Boot write protection status registers	BOOT_WP_STATUS	1	R	[174]	0x0
Boot area write protection register	BOOT_WP	1	R/W & R/W/ C_P	[173]	0x0
Reserved ¹		1	TBD	[172]	–
User area write protection register	USER_WP	1	R/W, R/W/ C_P & R/W/ E_P	[171]	0x0
Reserved ¹		1	TBD	[170]	–
FW configuration	FW_CONFIG	1	R/W	[169]	0x0
RPMB Size	RPMB_SIZE_MULT		R	[168]	0x20
Write reliability setting register	WR_REL_SET		R/W	[167]	0x1F
Write reliability parameter register	WR_REL_PARAM		R	[166]	0x5
Start Sanitize operation	SANITIZE_START	1	W/E_ P	[165]	0x0
Manually start background operations	BKOPS_START	1	W/E_ P	[164]	0x0

Enable background operations handshake	BKOPS_EN		R/W	[163]	0x0
H/W reset function	RST_n_FUNCTION	1	R/W	[162]	0x0
HPI management	HPI_MGMT	1	R/W/ E_P	[161]	0x0
Partitioning Support	PARTITIONING_SUPPORT	1	R	[160]	0x3
Max Enhanced Area Size	MAX_ENH_SIZE_MULT	3	R	[159:157]	0x0F951
Partitions attribute	PARTITIONS_ATTRIBUTE	1	R/W	[156]	0x0
Partitioning Setting	PARTITION_SETTING_COMPLETED	1	R/W	[155]	0x0
General Purpose Partition Size	GP_SIZE_MULT	12	R/W	[154:143]	0x0
Enhanced User Data Area Size	ENH_SIZE_MULT	3	R/W	[142:140]	0x0
Enhanced User Data Start Address	ENH_START_ADDR	4	R/W	[139:136]	0x0
Reserved ¹		1	TBD	[135]	-
Bad Block Management mode	SEC_BAD_BLK_MGMNT	1	R/W	[134]	0x0
Production state awareness	PRODUCTION_STATE_AWARENESS	1	R/W/ E	[133]	0x0
Package Case Temperature is controlled	TCASE_SUPPORT	1	W/E_ P	[132]	0x0
Periodic Wake-up	PERIODIC_WAKEUP	1	R/W/ E	[131]	0x0
Program CID/CSD in DDR mode support	PROGRAM_CID_CSD_DDR_SUPPORT	1	R	[130]	0x0
Reserved ¹	-	2	-	[129:128]	-
Vendor Specific Fields	VENDOR_SPECIFIC_FIELD	64	vend or speci fic	[127:64]	0x0
Native sector size	NATIVE_SECTOR_SIZE	1	R	[63]	0x0
Sector size emulation	USE_NATIVE_SECTOR	1	R/W	[62]	0x0
Sector size	DATA_SECTOR_SIZE	1	R	[61]	0x0
1st initialization after disabling sector size emulation	INI_TIMEOUT_EMU	1	R	[60]	0xA
Class 6 commands control	CLASS_6_CTRL	1	R/W/ E_P	[59]	0x0

			E_P		
Number of addressed group to be Released	DYNCAP_NEEDED	1	R	[58]	0x0
Exception events control	EXCEPTION_EVENTS_CTRL	2	R/W/ E_P	[57:56]	0x0
Exception events status	EXCEPTION_EVENTS_STATUS	2	R	[55:54]	0x0
Extended Partitions Attribute	EXT_PARTITIONS_ATTRIBUTE	2	R/W	[53:52]	0x0
Context configuration	CONTEXT_CONF	15	R/W/ E_P	[51:37]	0x0
Packed command status	PACKED_COMMAND_STATUS	1	R	[36]	0x0
Packed command failure index	PACKED_FAILURE_INDEX	1	R	[35]	0x0
Power Off Notification	POWER_OFF_NOTIFICATION	1	R/W/ E_P	[34]	0x0
Control to turn the Cache ON/OFF	CACHE_CTRL	1	R/W/ E_P	[33]	0x0
Flushing of the cache	FLUSH_CACHE	1	W/E_ P	[32]	0x0
Reserved ¹		1	TBD	[31]	0x0
Mode config	MODE_CONFIG	1	R/W/ E_P	[30]	0x0
Mode operation codes	MODE_OPERATION_CODES	1	W/E_ P	[29]	0x0
Reserved ¹		1	TBD	[28:27]	0x0
FFU status	FFU_STATUS	1	R	[26]	0x0
Pre loading data size	PRE_LOADING_DATA_SIZE	4	R/W/ E_P	[25:22]	0x0
Max pre loading data size	MAX_PRE_LOADING_DATA_SIZE	4	R	[21:18]	8GB: 0x00706147
Product state awareness enablement	PRODUCT_STATE_AWARENESS_ENABLEMENT	1	R/W/ E & R	[17]	0x3
Secure Removal Type	SECURE_REMOVAL_TYPE	1	R/W & R	[16]	0x0
Reserved ¹	-	16	-	[15:0]	-

6. eMMC AC Parameter

6.1 Timing Parameter

Timing Parameter		Max. Value	Unit
Initialization Time(tINIT)	Normal	1	s
	After partition setting	1	s
Read Timeout		100	ms
Write Timeout		250	ms
Erase Timeout		100	ms
Force Erase Timeout		3	Min
Secure Erase Timeout		22	s
Secure Trim step1 Timeout		5	s
Secure Trim step2 Timeout		17	s
Trim Timeout		900	ms
Partition Switching Timeout (after Init)		1.6	ms
Power Off Notification(short) Timeout		100	ms
Power Off Notification(long) Timeout		600	ms

6.2 Bus Timing Specification in HS400 mode

6.2.1 HS400 Device Input Timing

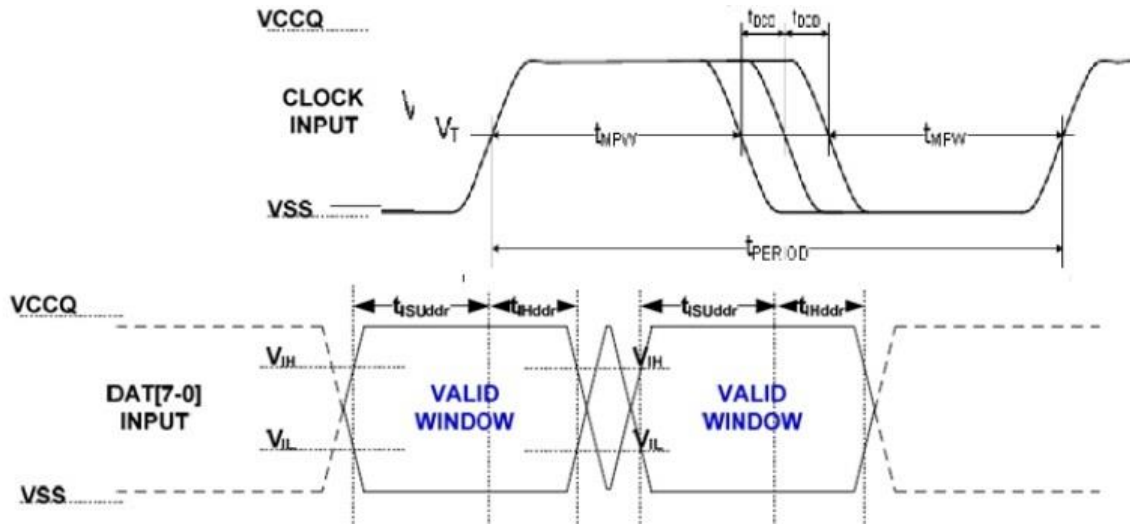
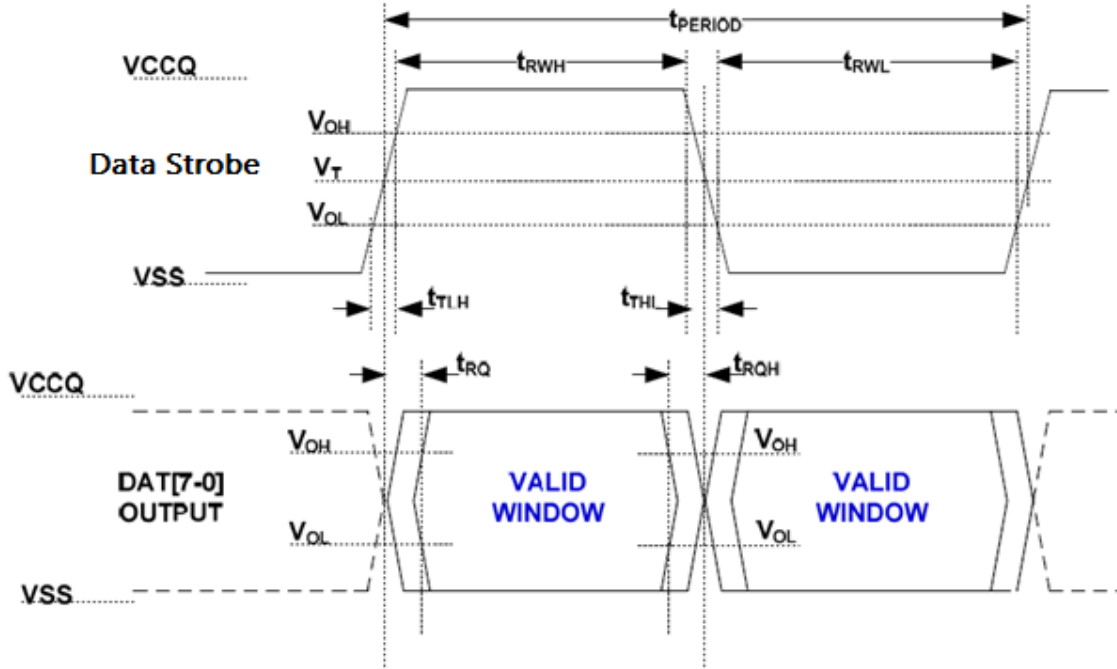


Figure 5 HS400 Device Input Timing

[Table 6] HS400 Device Input Timing

Parameter	Symbol	Min	Max	Unit	Remark
Input CLK					
Cycle time data transfer mode	t _{PERIOD}	5			200MHz(Max), between rising edges With respect to V _T .
Slew rate	SR	-1.125		V/ns	With respect to V _T
Duty cycle distortion	t _{CKDCC}	0.0	0.3	ns	Allowable deviation from an ideal 50% duty cycle. With respect to V _T . Includes jitter, phase noise
Minimum pulse width	t _{CKMPW}	2.2		ns	With respect to V _T .
Input DAT (referenced to CLK)					
Input set-up time	t _{ISUddr}	0.4		ns	C _{Device} ≤ 6pF With respect to V _{IH} /V _{IL} .
Input hold time	t _{IHddr}	0.4		ns	C _{Device} ≤ 6pF With respect to V _{IH} /V _{IL} .
Slew rate	SR	1.125		V/ns	With respect to V _{IH} /V _{IL} .

6.2.2 HS400 Device Output Timing



Note: V_{OH} denotes $V_{OH(min)}$ and V_{OL} denotes $V_{OL(max)}$.

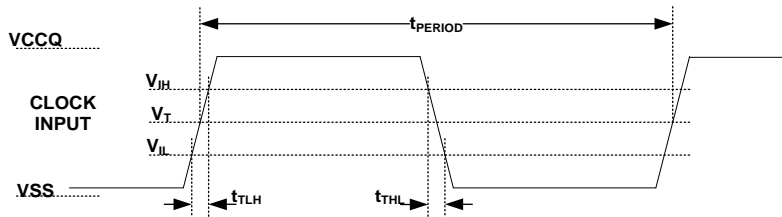
Figure 6 HS400 Device Output Timing

[Table 7]HS400 Device Output Timing

Parameter	Symbol	Min	Max	Unit	Remark
Data Strobe					
Cycle time data transfer mode	t_{PERIOD}	5			200MHz(Max), between rising edges With respect to V_T
Slew rate	SR	-1.125		V/ns	With respect to V_{OH}/V_{OL} and HS400 reference load
Duty cycle distortion	t_{DSDCD}	0.0	0.2	ns	Allowable deviation from the input CLK timing. With respect to V_T Includes jitter, phase noise
Minimum pulse width	t_{DSMPW}	2.0		ns	With respect to V_T
Read pre-amble	t_{RPRE}	0.4	-	t_{PERIOD}	Max value is specified by manufacturer. Value up to infinite is valid
Read post-amble	t_{RPST}	0.4	-	t_{PERIOD}	Max value is specified by manufacturer. Value up to infinite is valid
Output DAT (referenced to Data Strobe)					
Output skew	t_{RQ}		0.4	ns	With respect to V_{OH}/V_{OL} and HS400 reference load
Output hold skew	t_{RQH}		0.4	ns	With respect to V_{OH}/V_{OL} and HS400 reference load.
Slew rate	SR	1.125		V/ns	With respect to V_{OH}/V_{OL} and HS400 reference load

6.3 Bus Timing Specification in HS200 mode

6.3.1 HS200 Device Clock Timing



Note1: V_{IH} denote $V_{IH(min.)}$ and V_{IL} denotes $V_{IL(max.)}$.

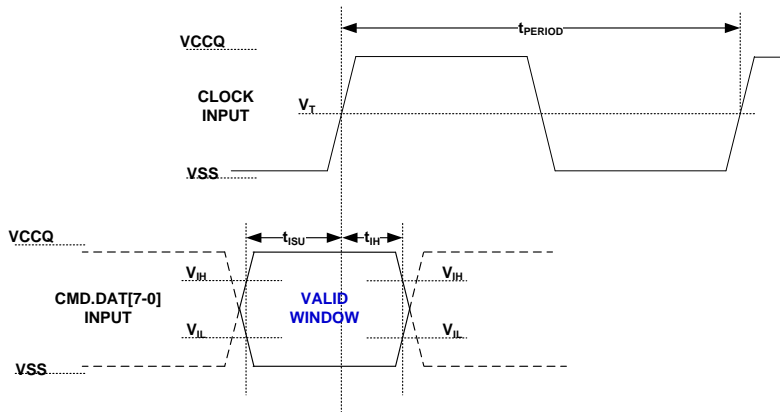
Note2: $V_T=0.975V$ - Clock Threshold ($V_{CCQ} = 1.8V$) and $V_T=0.65V$ - Clock Threshold ($V_{CCQ} = 1.2V$), indicates clock reference point for timing measurements.

[Table 8]HS200 Device Clock Timing

Symbol	Min.	Max.	Unit	Remark
t_{PERIOD}	5	-	ns	200MHz (Max.), between rising edges
t_{TLH}, t_{THL}	-	$0.2 \cdot t_{PERIOD}$	ns	$t_{TLH}, t_{THL} < 1ns$ (max.) at 200MHz, $C_{DEVICE}=6pF$, The absolute maximum value of t_{TLH}, t_{THL} is 10ns regardless of clock frequency.
Duty Cycle	30	70	%	

Figure 7 HS200 Device Clock Timing

6.3.2 HS200 Device Input Timing



Note1: t_{ISU} and t_{IH} are measured at $V_{IL(max.)}$ and $V_{IH(min.)}$.

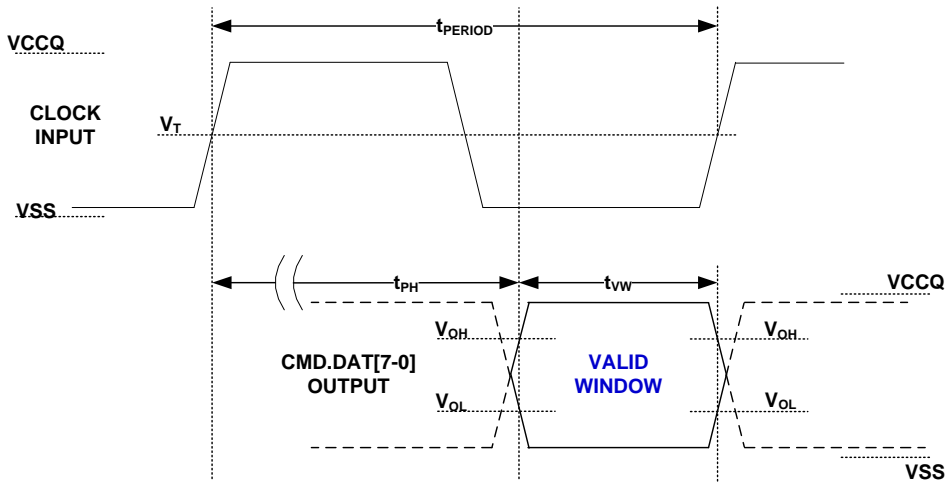
Note2: V_{IH} denote $V_{IH(min.)}$ and V_{IL} denotes $V_{IL(max.)}$.

Figure 8 HS200 Device Input Timing

[Table 9]HS200 Device Input Timing

Symbol	Min.	Max.	Unit	Remark
t_{ISU}	1.40	-	ns	$C_{DEVICE} \leq 6pF$
t_{IH}	0.8		ns	$C_{DEVICE} \leq 6pF$

6.3.3 HS200 Device Output Timing



Note: V_{OH} denotes $V_{OH}(\min.)$ and V_{OL} denotes $V_{OL}(\max.)$.

Figure 9 HS200 Device Output Timing

[Table 10] HS200 Device Output Timing

Symbol	Min.	Max.	Unit	Remark
t_{PH}	0	2	UI	Device output momentary phase from CLK input to CMD or DAT lines output. Does not include a long term temperature drift.
ΔT_{PH}	-350 ($\Delta T = -20$ deg.C)	+1550 ($\Delta T = 90$ deg.C)	ps	Delay variation due to temperature change after tuning. Total allowable shift of output valid window (T_{VW}) from last system Tuning procedure ΔT_{PH} is 2600ps for ΔT from -25 deg.C to 125 deg.C during operation.
t_{VW}	0.575	-	UI	$t_{VW} = 2.88ns$ at 200MHz Using test circuit in Figure 6 including skew among CMD and DAT lines created by the Device. Host path may add Signal Integrity induced noise, skews, etc. Expected T_{VW} at Host input is larger than 0.475UI.

Note: Unit Interval (UI) is one bit nominal time. For example, UI=5ns at 200MHz.

7. eMMC DC Parameter

7.1 Supply Voltage

[Table 11] Supply voltage

Item	Min	Max	Unit
V _{CCQ}	1.70(2.7)	1.95(3.6)	V
V _{CC}	2.7	3.6	V
V _{SS}	-0.5	0.5	V

7.2 Bus Signal Line Load

[Table 12] Bus Signal Line Load

Parameter	Symbol	Min	Typ.	Max	Unit	Remark
Pull-up resistance for CMD	R _{CMD}	4.7		100	KOhm	to prevent bus floating
Pull-up resistance for DAT0-DAT7	R _{DAT}	10		100	KOhm	to prevent bus floating
Internal pull up resistance DAT1-DAT7	R _{int}	10		150	KOhm	to prevent unconnected lines floating
Single e · MMC capacitance	C _{BGA}			12	pF	
Maximum single line inductance				16	nH	F _{pp} ≤52MHz

[Table 13] Capacitance and Resistance for HS400 mode

Parameter	Symbol	Min	Typ.	Max	Unit	Remark
Bus signal line capacitance	CL			13	pF	Single Device
Single Device capacitance	C _{DEVICE}			6	pF	
Pull-down resistance for Data Strobe	R _{Data Strobe}	10		100	Kohm	

8. Ordering Information

[Table 14] Ordering Information

Capacity	eMMC P/N	Package Size	Pin
8GB	MKEV008GIB-NY500	11.5mmx13mmx1.0mm	153 FBGA